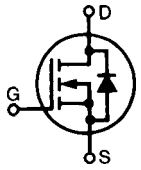
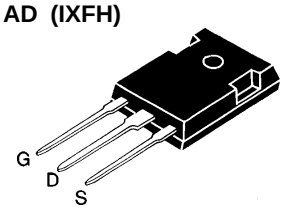
HiPerFET™ Power MOSFETs

N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family

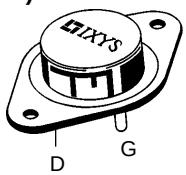
	V_{DSS}	I_{D25}	$R_{DS(on)}$	t_{rr}
IXFH/FM 10N100	1000 V	10 A	1.20 Ω	250 ns
IXFH/FM 12N100	1000 V	12 A	1.05 Ω	250 ns



TO-247 AD (IXFH)



TO-204 AA (IXFM)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		1000	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ		1000	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C	10N100	10	A
		12N100	12	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	10N100	40	A
		12N100	48	A
I_{AR}	T_C = 25°C	10N100	10	A
		12N100	12	A
E_{AR}	T_C = 25°C		30	mJ
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		300	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s			300	°C

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
V_{DSS}	V_{GS} = 0 V, I_D = 3 mA		1000			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA		2.0		4.5	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0				±100	nA
I_{DSS}	V_{DS} = 0.8 V_{DSS}	T_J = 25°C			250	µA
	V_{GS} = 0 V	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 I_{D25}	10N100			1.20	Ω
		12N100			1.05	Ω
	Pulse test, t ≤ 300 µs, duty cycle δ ≤ 2 %					

Features

- International standard packages
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

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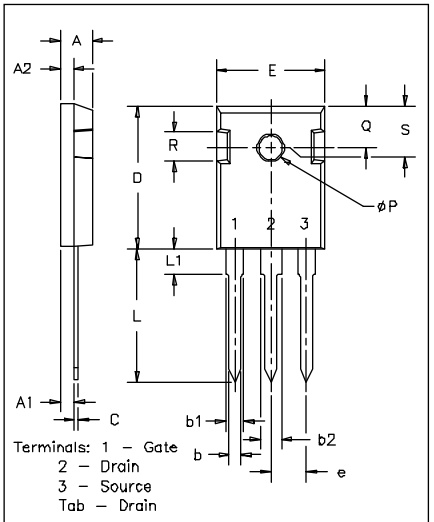
Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 I_{D25}, pulse test	6	10		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4000		pF
C_{oss}			310		pF
C_{rss}			70		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25} R_G = 2 Ω (External),		21	50	ns
t_r			33	50	ns
$t_{d(off)}$			62	100	ns
t_f			32	50	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		122	155	nC
Q_{gs}			30	45	nC
Q_{gd}			50	80	nC
R_{thJC}				0.42	K/W
R_{thCK}			0.25		K/W

Source-Drain Diode

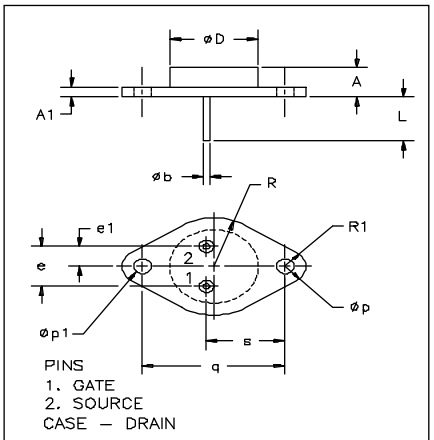
Symbol	Test Conditions		Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0	10N100			10	A
		12N100			12	A
I_{SM}	Repetitive; pulse width limited by T_{JM}	10N100			40	A
		12N100			48	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle δ ≤ 2 %				1.5	V
t_{rr}	I_F = I_S -di/dt = 100 A/µs, V_R = 100 V	T_J = 25°C			250	ns
		T_J = 125°C			400	ns
Q_{RM}		T_J = 25°C		1		µC
		T_J = 125°C		2		µC
I_{RM}		T_J = 25°C		10		A
		T_J = 125°C		15		A

TO-247 AD (IXFH) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.7	5.3
A_1	.087	.102	2.2	2.54
A_2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b_1	.065	.084	1.65	2.13
b_2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
øP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

TO-204 AA (IXFM) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.250	.450	6.4	11.4
A1		.135		3.42
øb	.038	.043	.97	1.09
øD		.875		22.22
e	.420	.440	10.67	11.17
e1	.205	.225	5.21	5.71
L	.312		7.93	
øp	.151	.165	3.84	4.19
øp1	.151	.165	3.84	4.19
q	1.187 BSC		30.15 BSC	
R		.525		13.33
R1		.188		4.77
s	.655	.675	16.64	17.14

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Fig.1. Output Characteristics

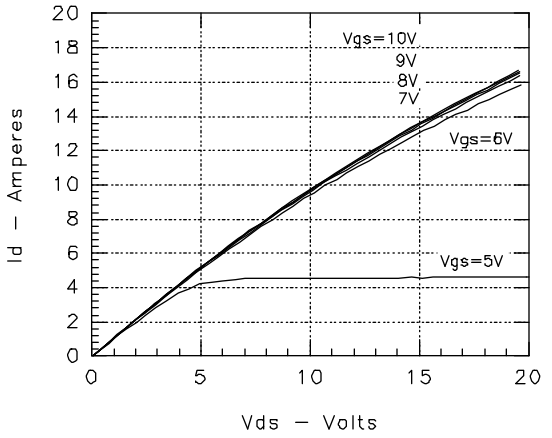

Fig. 2. Input Admittance

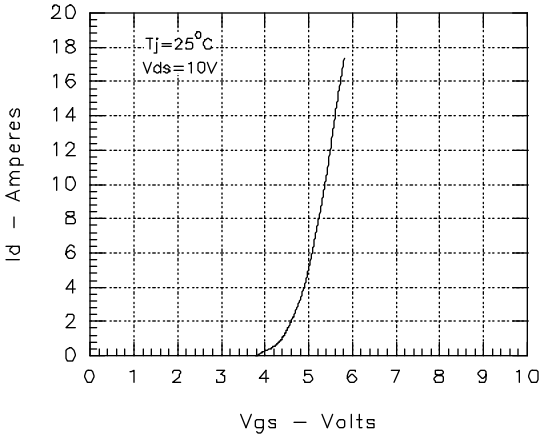

Fig. 3. Rds(on) vs. Drain Current

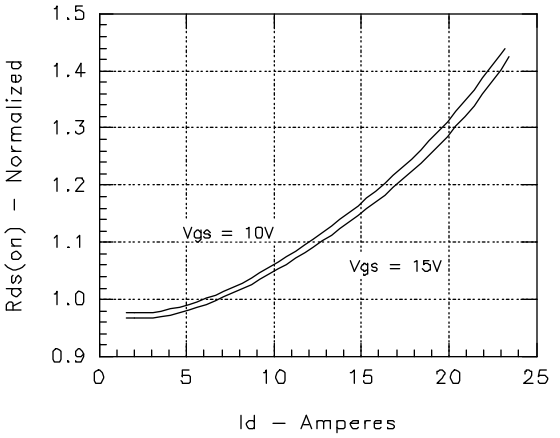

Fig. 4. Temperature Dependence of Drain to Source Resistance

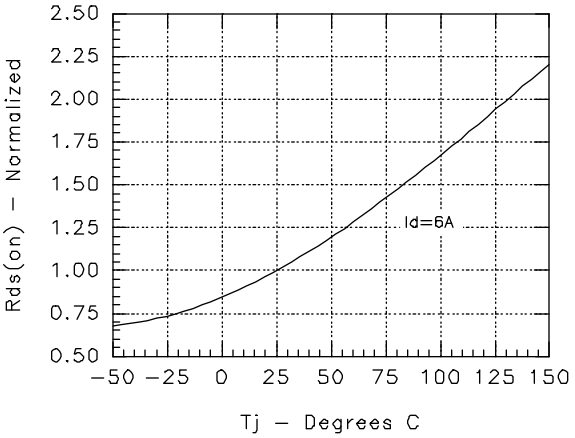

Fig. 5. Drain Current vs. Case Temperature

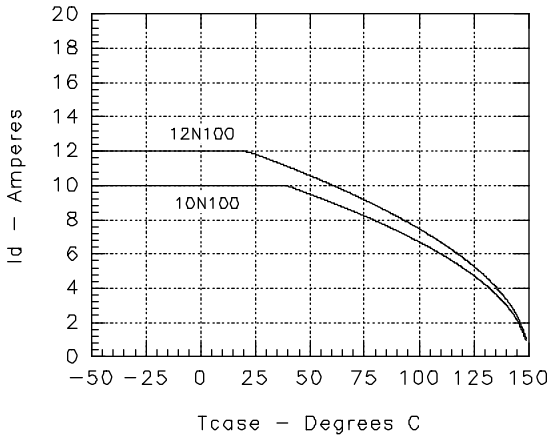

Fig. 6. Temperature Dependence of Breakdown Voltage and Threshold Voltage

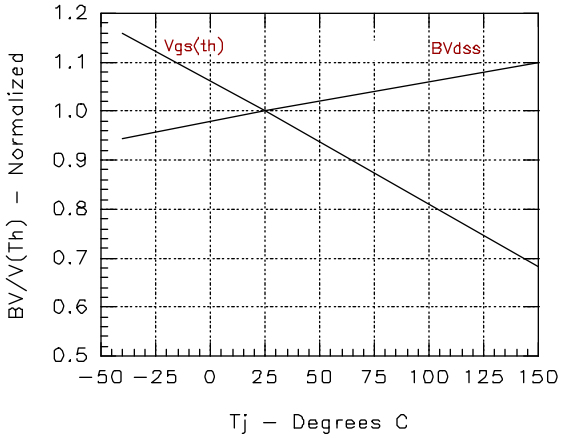

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Fig. 7. Gate Charge

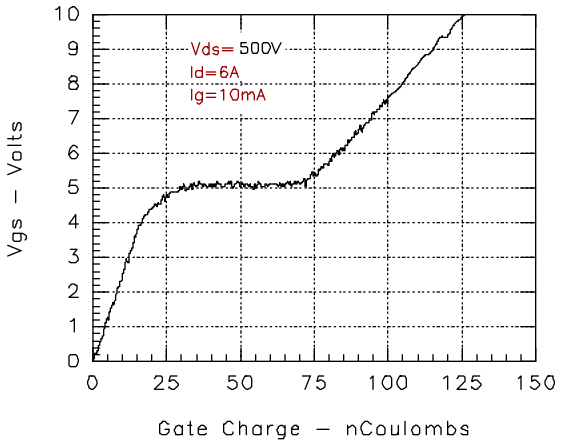


Fig. 8. Forward Bias Safe Operating Area

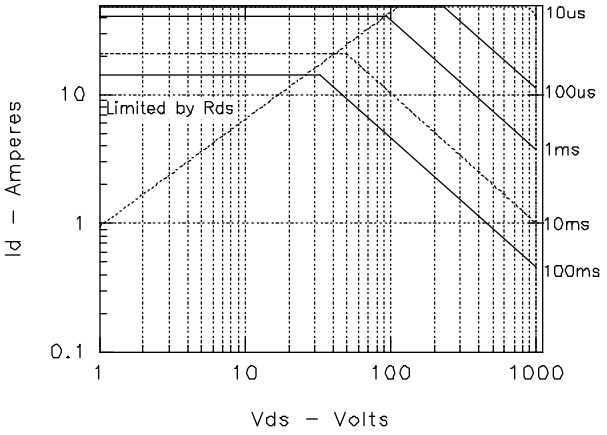


Fig. 9. Capacitance Curves

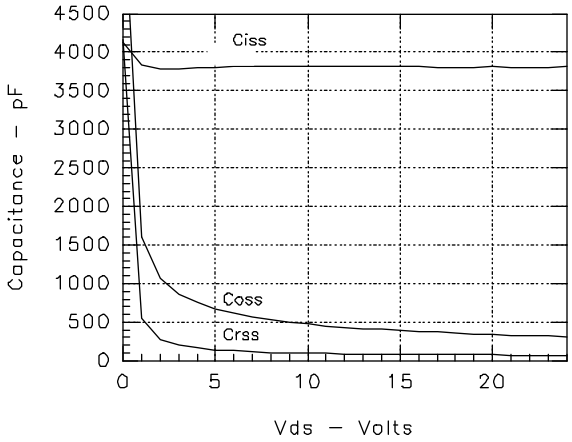


Fig. 10. Source Current vs. Source to Drain Voltage

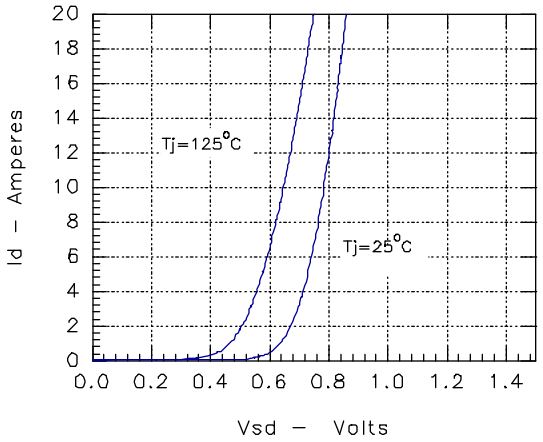
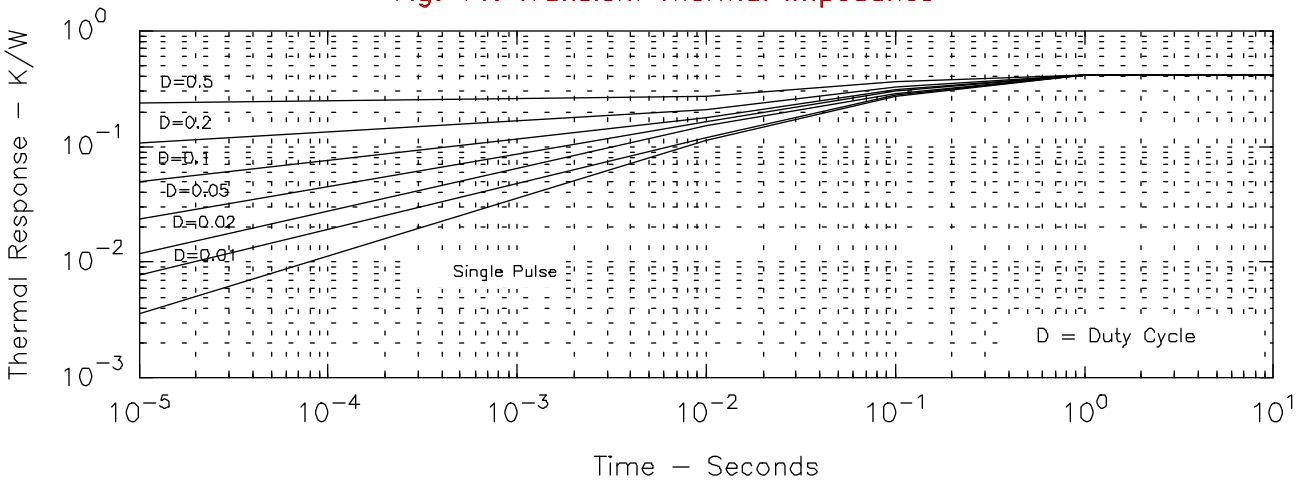


Fig. 11. Transient Thermal Impedance



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